20 V, 2 A PNP medium power transistors Rev. 7 — 12 October 2011

1. **Product profile**

1.1 General description

PNP medium power transistor series in Surface-Mounted Device (SMD) plastic packages.

Product overview Table 1.

Type number ^[1]	Package	NPN complement		
	NXP	JEITA	JEDEC	
BCP69	SOT223	SC-73	-	BCP68
BC869	SOT89	SC-62	TO-243	BC868
BC69PA	SOT1061	-	-	BC68PA

[1] Valid for all available selection groups.

1.2 Features and benefits

- High current
- Three current gain selections
- High power dissipation capability
- Exposed heatsink for excellent thermal and electrical conductivity (SOT89, SOT1061)
- Leadless very small SMD plastic package with medium power capability (SOT1061)
- AEC-Q101 gualified

1.3 Applications

- Linear voltage regulators
- High-side switches
- Battery-driven devices
- Power management

- MOSFET drivers
- Amplifiers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-20	V
I _C	collector current		-	-	-2	А
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	-3	А



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Table 2.	Quick reference data continued							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
h _{FE}	DC current gain	$V_{CE} = -1 V;$ $I_{C} = -500 mA$	<u>[1]</u> 85	-	375			
	h _{FE} selection -16	$V_{CE} = -1 V;$ $I_{C} = -500 mA$	[<u>1]</u> 100	-	250			
	h _{FE} selection -25	$V_{CE} = -1 V;$ $I_{C} = -500 mA$	<u>[1]</u> 160	-	375			

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta = 0.02$.

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
SOT223			
1	base		
2	collector		2, 4
3	emitter		1
4	collector		3 sym028
SOT89			
1	emitter		_
2	collector		2
3	base		3
SOT1061			
1	base		2
2	emitter	3	3
3	collector		1
		Transparent top view	

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3. Ordering information

Table 4. Ordering information					
Type number ^[1]	Package				
	Name	Description	Version		
BCP69	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		
BC869	SC-62	plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads	SOT89		
BC69PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body $2 \times 2 \times 0.65$ mm	SOT1061		

[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes	
Type number	Marking code
BCP69	BCP69
BCP69-16	BCP69/16
BCP69-25	BCP69/25
BC869	CEC
BC869-16	CGC
BC869-25	СНС
BC69PA	B3
BC69-16PA	BM
BC69-25PA	BN

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5. Limiting values

Table 6. In accordar	Limiting values nce with the Absolute Maximur	n Rating System (IEC	C 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-32	V
V _{CEO}	collector-emitter voltage	open base	-	-20	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current		-	-2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-3	A
I _B	base current		-	-0.4	А
I _{BM}	peak base current	single pulse; $t_p \leq 1 ms$	-	-0.4	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	BCP69		<u>[1]</u> _	0.65	W
			[2]	1.00	W
			<u>[3]</u>	1.35	W
	BC869		<u>[1]</u> _	0.50	W
			[2]	0.95	W
			<u>[3]</u>	1.35	W
	BC69PA		<u>[1]</u> _	0.42	W
			[2]	0.83	W
			[3]	1.10	W
			<u>[4]</u>	0.81	W
			<u>[5]</u>	1.65	W
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

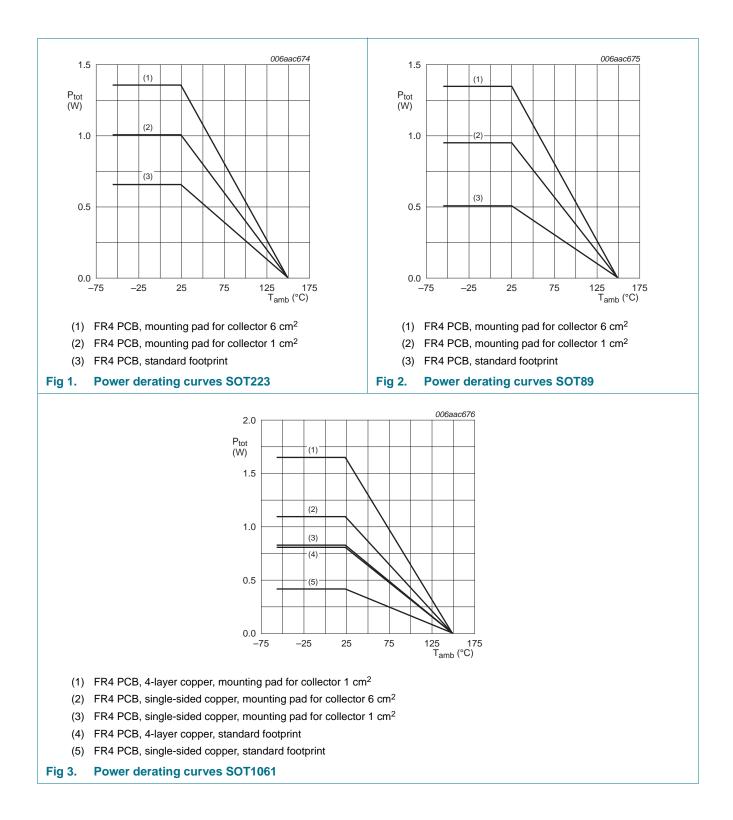
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

BCP69; BC869; BC69PA



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6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	BCP69		<u>[1]</u> -	-	192	K/W
			[2] _	-	125	K/W
			[3] _	-	93	K/W
	BC869		<u>[1]</u> -	-	250	K/W
			[2] _	-	132	K/W
			[3] _	-	93	K/W
	BC69PA		<u>[1]</u> -	-	298	K/W
			[2] _	-	151	K/W
			[3] _	-	114	K/W
			[4] _	-	154	K/W
			<u>[5]</u> _	-	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point					
	BCP69		-	-	16	K/W
	BC869		-	-	16	K/W
	BC69PA		-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

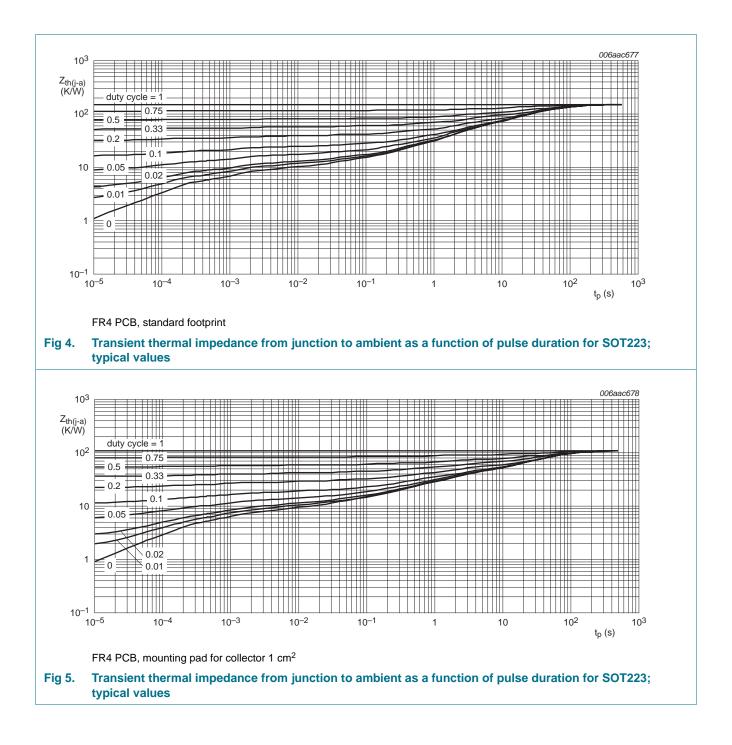
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

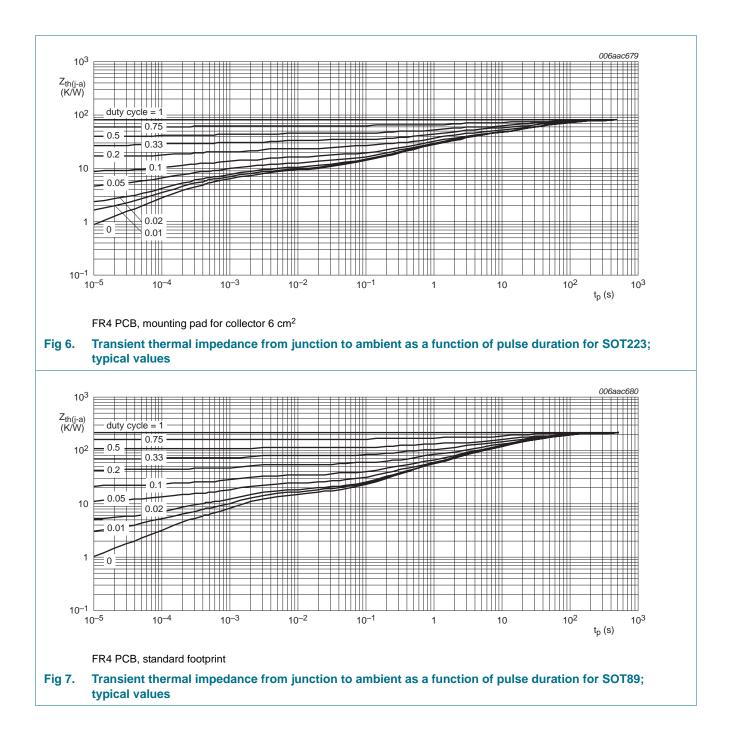
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

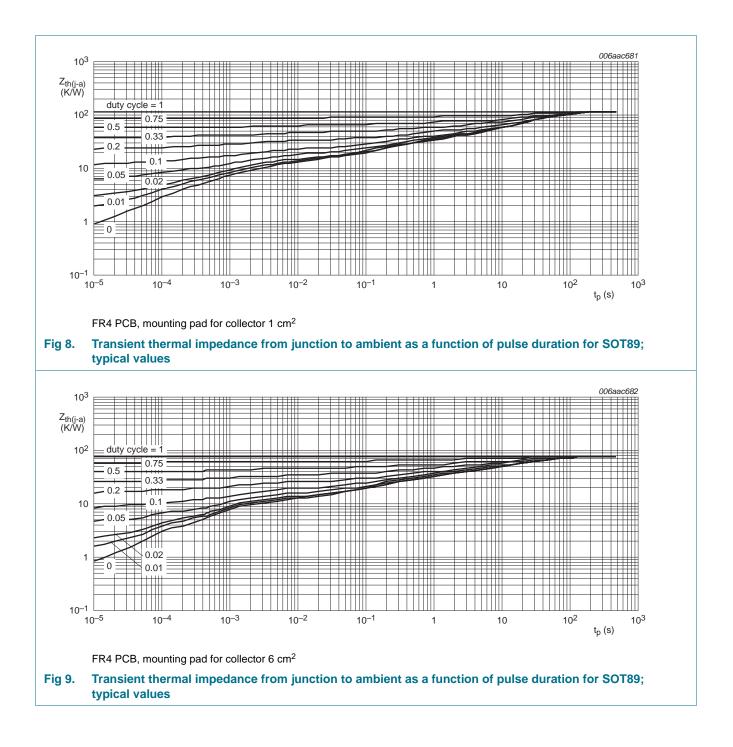
BCP69; BC869; BC69PA



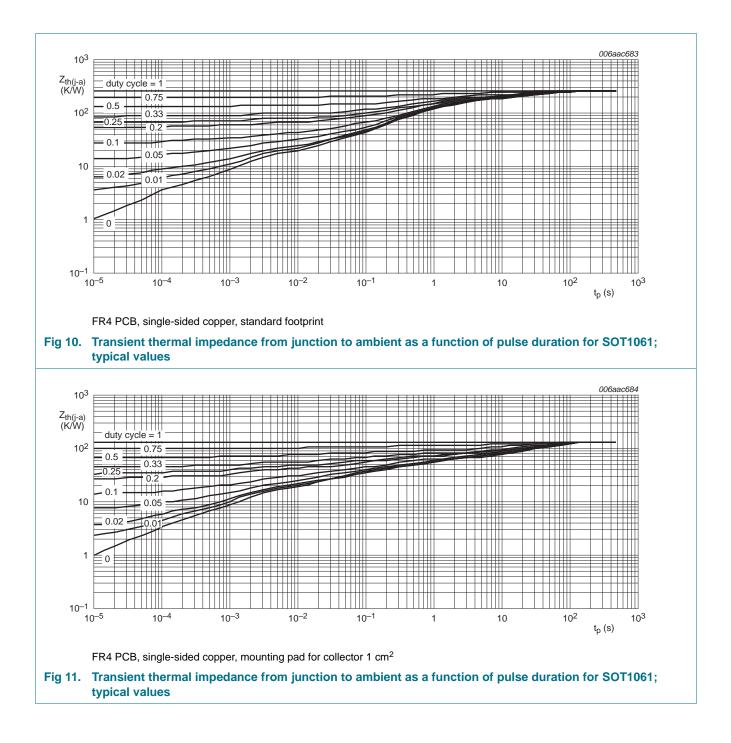
BCP69; BC869; BC69PA



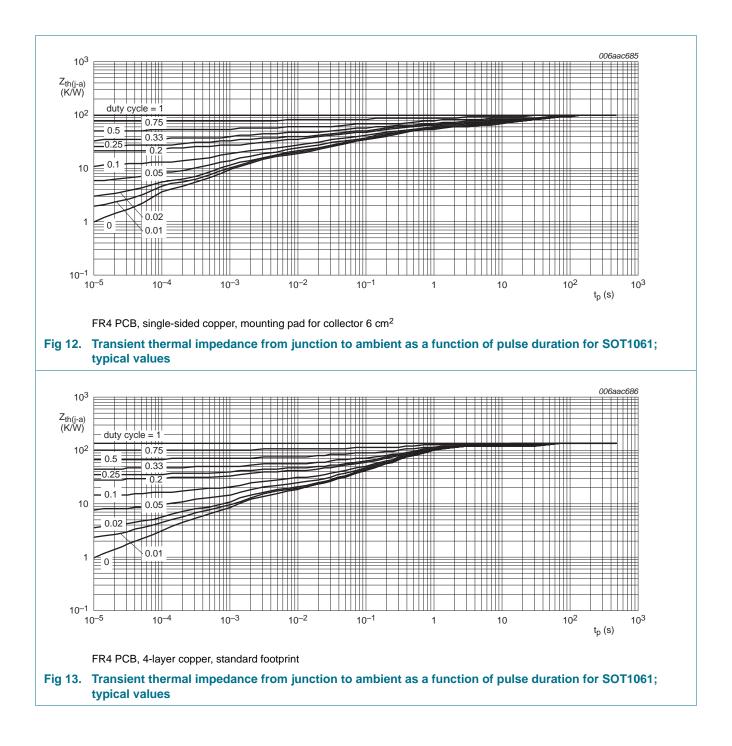
BCP69; BC869; BC69PA



BCP69; BC869; BC69PA

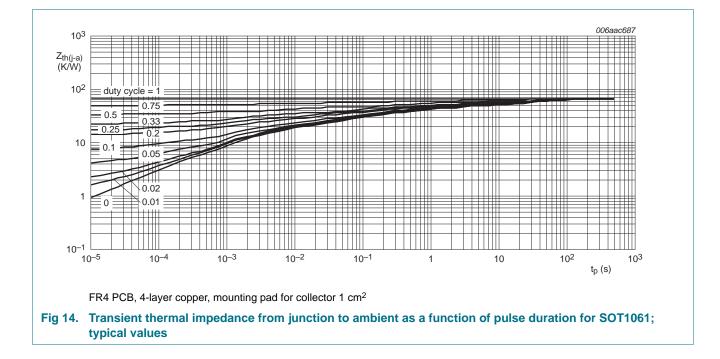


BCP69; BC869; BC69PA



BCP69; BC869; BC69PA

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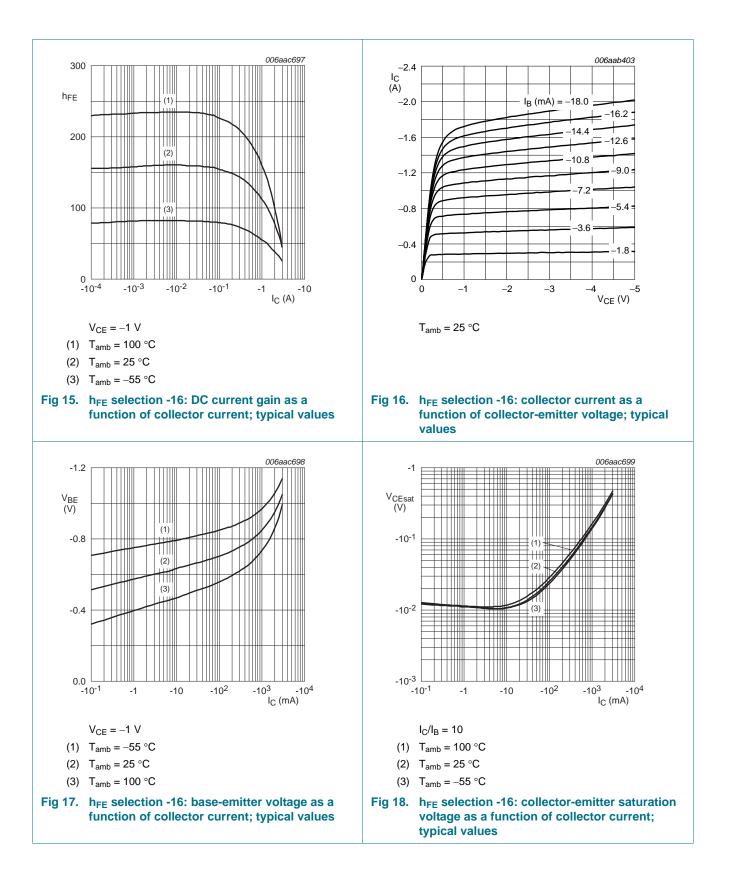
7. Characteristics

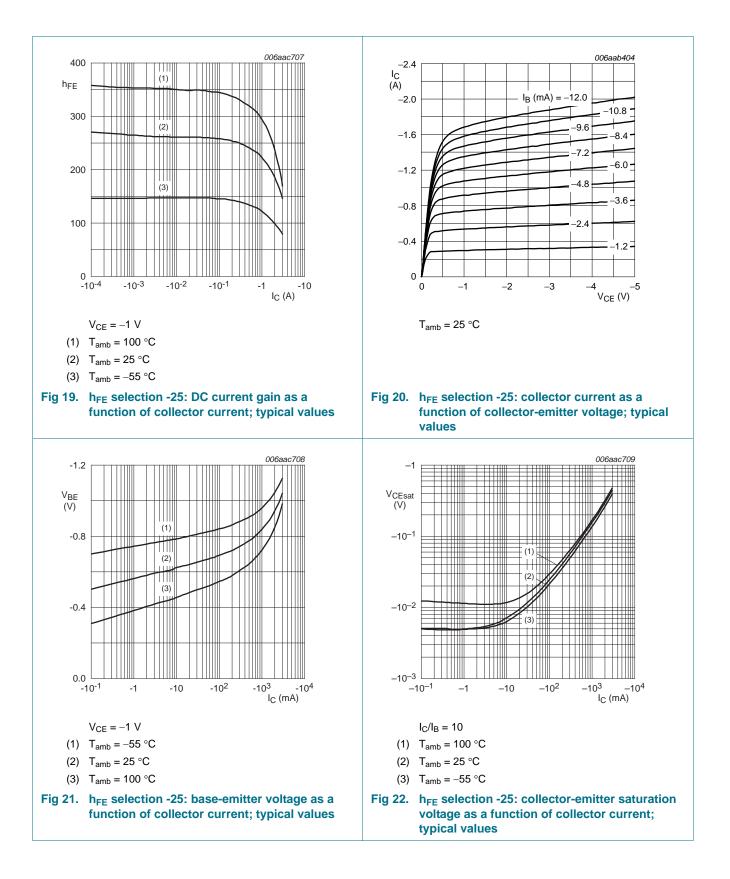
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V_{CB} = -25 V; I _E = 0 A		-	-	-100	nA
current	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = -25 \; V; \; I_{E} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$		-	-	-10	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -10 V$					
		$I_C = -5 \text{ mA}$		50	-	-	
	DC current gain	$V_{CE} = -1 V$					
		$I_{C} = -500 \text{ mA}$	<u>[1]</u>	85	-	375	
		$I_{\rm C} = -1$ A	<u>[1]</u>	60	-	-	
		$I_{\rm C} = -2$ A	[1]	40	-	-	
	DC current gain	$V_{CE} = -1 V$					
	h _{FE} selection -16	$I_{C} = -500 \text{ mA}$	<u>[1]</u>	100	-	250	
	h _{FE} selection -25	$I_{C} = -500 \text{ mA}$	<u>[1]</u>	160	-	375	
V _{CEsat}	collector-emitter	$I_{C} = -1 \text{ A}; I_{B} = -100 \text{ mA}$	<u>[1]</u>	-	-	-0.5	V
	saturation voltage	$I_{C} = -2 \text{ A}; I_{B} = -200 \text{ mA}$	[1]			-0.6	V
V _{BE}	base-emitter voltage	V_{CE} = -10 V; I _C = -5 mA	[1]	-	-	-0.7	V
		$V_{CE} = -1 V; I_C = -1 A$	[1]	-	-	-1	V
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB}=-10 \text{ V}; \text{ I}_{E}=\text{i}_{e}=0 \text{ A};\\ \text{ f}=1 \text{ MHz} \end{array}$		-	28	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_C = -50 \text{ mA};$ f = 100 MHz		40	140	-	MHz

[1] Pulse test: $t_p \leq 300 \ \mu s; \ \delta = 0.02.$

BCP69; BC869; BC69PA

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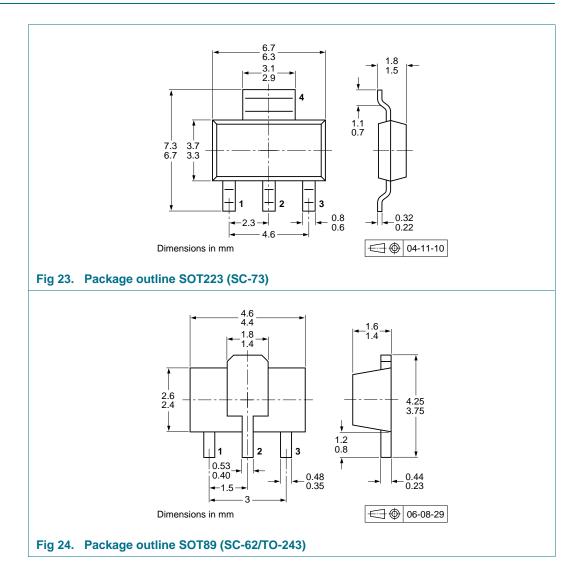
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8. Test information

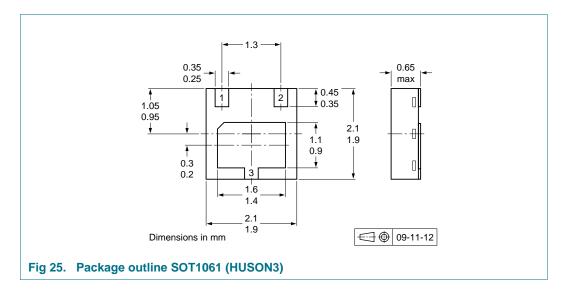
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Description	iption		Packing quantity		
number ^[2]				1000	3000	4000	
BCP69	SOT223	8 mm pitch, 12 mm tape and reel		-115	-	-135	
BC869	SOT89	8 mm pitch, 12 mm tape and reel; T1	[3]	-115	-	-135	
		8 mm pitch, 12 mm tape and reel; T3	[4]	-146	-	-	
BC69PA	SOT1061	4 mm pitch, 8 mm tape and reel		-	-115	-	

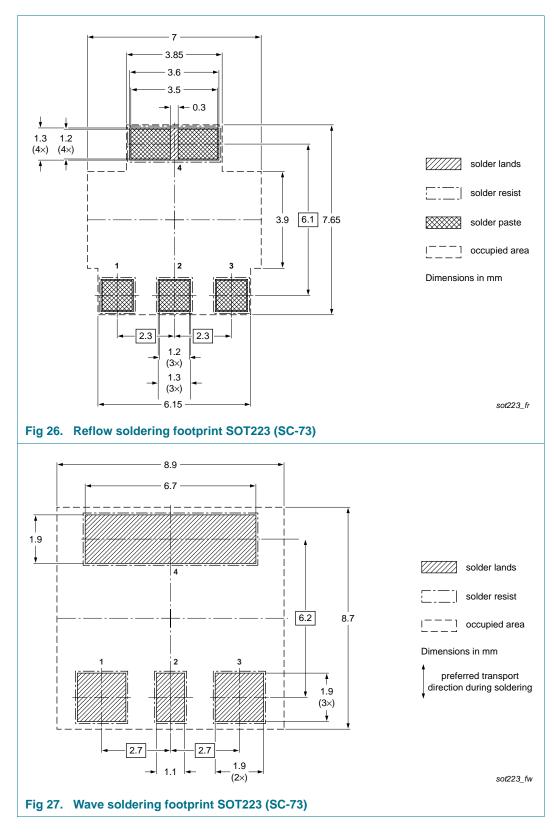
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] Valid for all available selection groups.

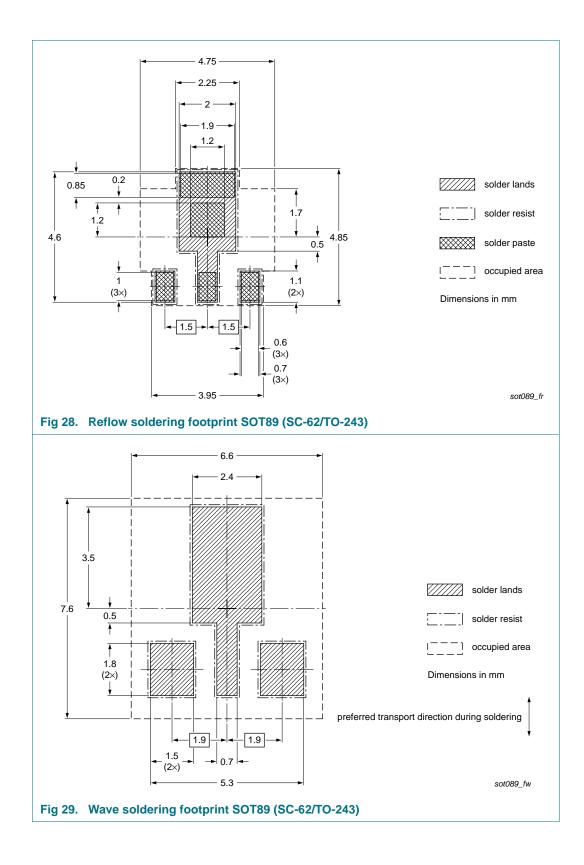
- [3] T1: normal taping
- [4] T3: 90° rotated taping

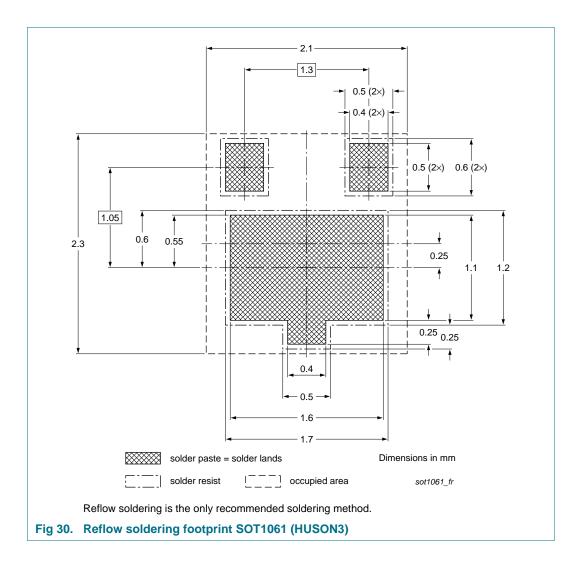
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11. Soldering



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12. Revision history

Table 10. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
BCP69_BC869_BC69PA v.7	20111012	Product data sheet	-	BC869_6 BCP69_6		
Modifications:		of this document has been of NXP Semiconductors.	n redesigned to co	mply with the new identity		
	 Legal texts 	have been adapted to the	new company nar	ne where appropriate.		
	 Type numb 	er BC69PA added				
	 Type numb 	er BCP69-16/DG and BCF	P69-16/IN removed	1		
	Section 1 "	Product profile": updated				
		Pinning information": upda				
	 <u>Section 3 "Ordering information"</u>: updated 					
	 <u>Section 4 "Marking"</u>: updated 					
	 <u>Section 10 "Packing information"</u>:updated 					
	 <u>Table 6</u>, <u>7</u> and <u>8</u>: updated according to latest measurements 					
		5 to 18 updated				
		<u>14, 24</u> to <u>25, 28</u> to <u>30</u> : add	led			
BC869_6	20041108	Product data sheet	-	BC869_5		
BC869_5	20031202	Product specification	-	BC869_4		
BC869_4	19990408	Product specification	-	BC869_3		
BC869_3	19980716	Product specification	-	BC869_CNV_2		
BC869_CNV_2	19970401	Product specification	-	-		
BCP69_6	20081202	Product data sheet	-	BCP69_5		
BCP69_5	20031125	Product specification	-	BCP69_4		
BCP69_4	20021115	Product specification	-	BCP69_3		
BCP69_3	19990408	Product specification	-	BCP69_CNV_2		
BCP69_CNV_2	19970312	Product specification	-	-		

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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Date of release: 12 October 2011 Document identifier: BCP69_BC869_BC69PA